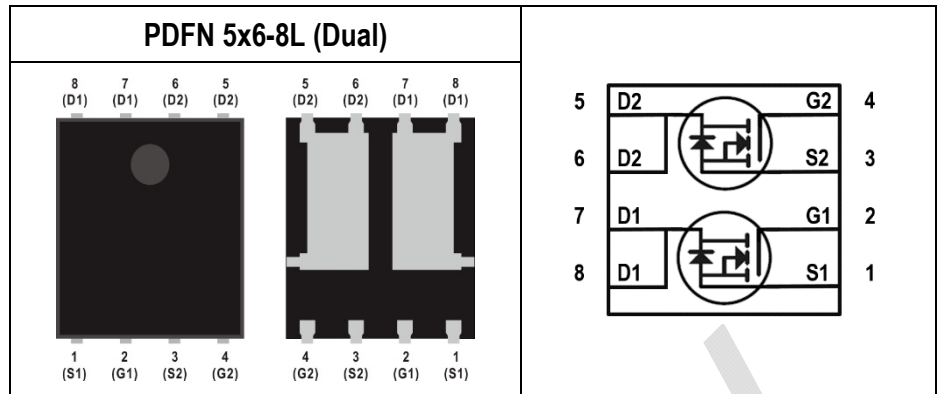


Parameter	Value	Unit
V_{DSS}	100	V
$R_{DS(ON) max. V_{GS}=10V}$	20	m Ω
I_D	18.3	A
Q_g	15.6	nC
Q_{gd}	5.6	nC
Q_{sw}	7.6	nC



Features	Application
<ul style="list-style-type: none"> Optimized for synchronous rectification Low Input Capacitance Low Miller Capacitance Fully Characterized Capacitance and Avalanche Pb-free lead plating; RoHS compliant 	<ul style="list-style-type: none"> BLDC Motor drive applications Battery powered circuits Synchronous rectifier applications Resonant mode power supplies

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
DG100N14HQD	Halogen-Free	PDFN 5x6-8L (Dual)	QD	Tape & Reel	2,500

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	100	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Drain Current-Continuous ^{Note 1}	I_D	$T_C=25^\circ\text{C}$	29.0	A
		$T_C=100^\circ\text{C}$	18.3	A
Drain Current-Pulsed ^{Note 2}	I_{DM}	46.2	A	
Avalanche Current	I_{AR}	15	A	
Single Pulse Avalanche Energy ^{Note 3}	E_{AS}	11.3	mJ	
Maximum Power Dissipation	P_D	26.6	W	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-Case ^{Note 4}	$R_{\theta JC}$	Steady State	-	-	4.7	$^\circ\text{C/W}$
Thermal resistance, Junction-Ambient ^{Note 4}	$R_{\theta JA}$	Steady State	-	-	54.5	$^\circ\text{C/W}$

Notes:

- Limited by silicon chip capability and $R_{\theta JC}$ junction-to-case thermal resistance.
- Must be ensure junction temperature does not exceed 150-degree C. (Pulse Width $\leq 10\text{ms}$, Duty $\leq 1\%$)
- Limited by T_{Jmax} , starting $T_J=25^\circ\text{C}$, $L=1\text{mH}$, $R_g=25\Omega$, $I_D=15\text{A}$, $V_{GS}=10\text{V}$.
- The value of thermal resistance is measured with the single device mounted on 1 inch² FR-4 PCB with 2 oz. copper under a still air environment temperature is 25 $^\circ\text{C}$ based on JEDEC standard JESD51-14 and JESD51-2a. Thermal resistance obtained depends on the user's specific board design and given application.

Electrical Characteristics (T_J=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _{DS} =1mA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	10	μA
		V _{DS} =100V, V _{GS} =0V, T _J =125°C	-	-	100	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

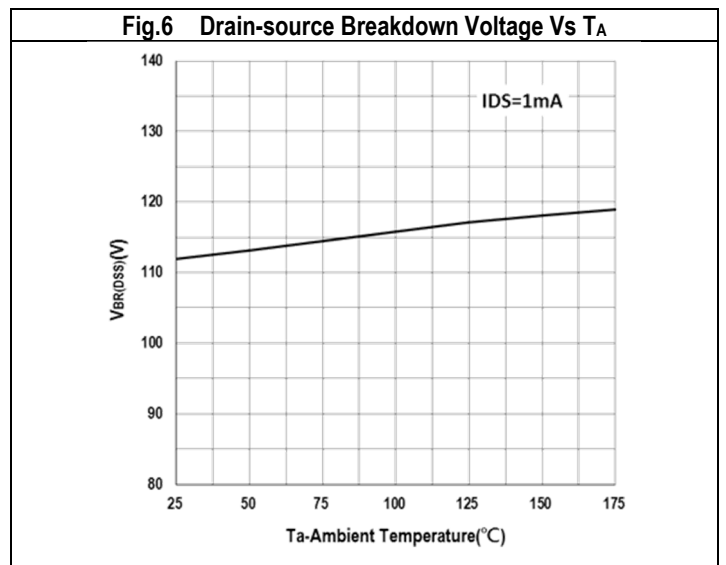
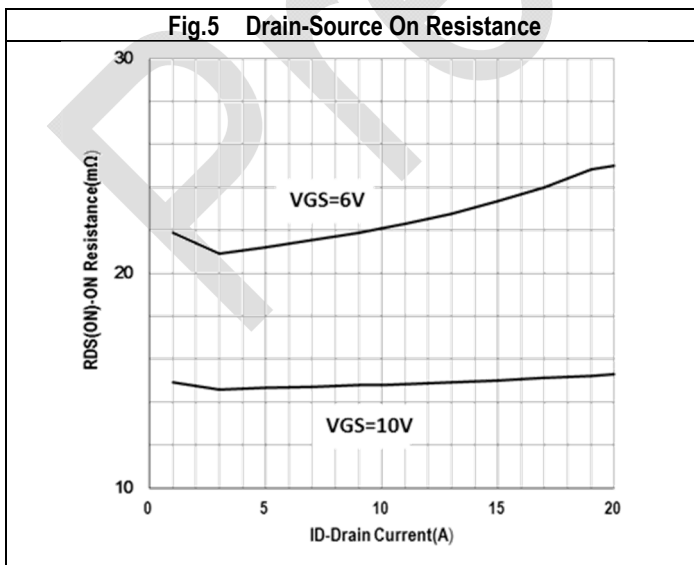
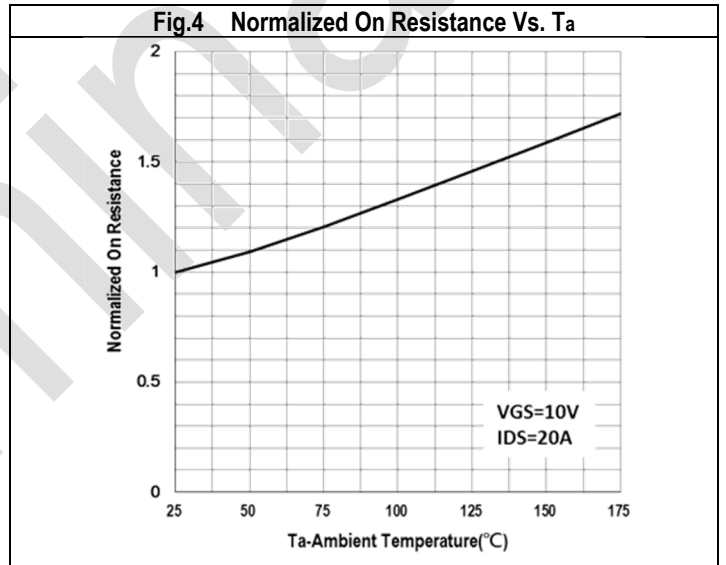
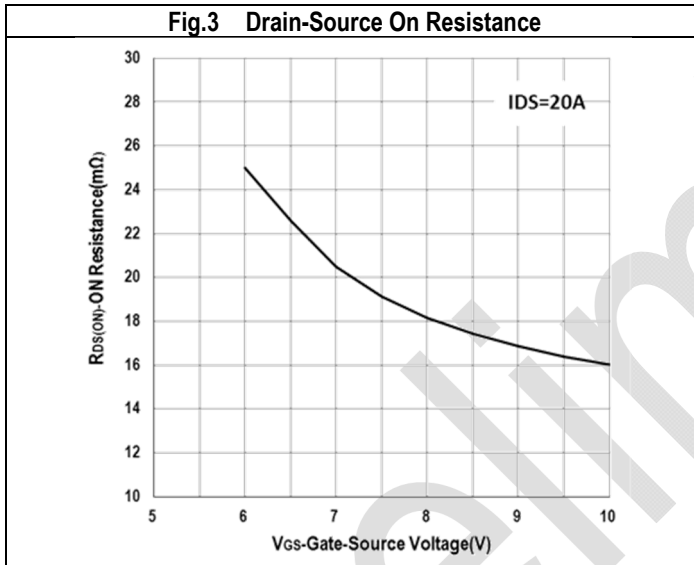
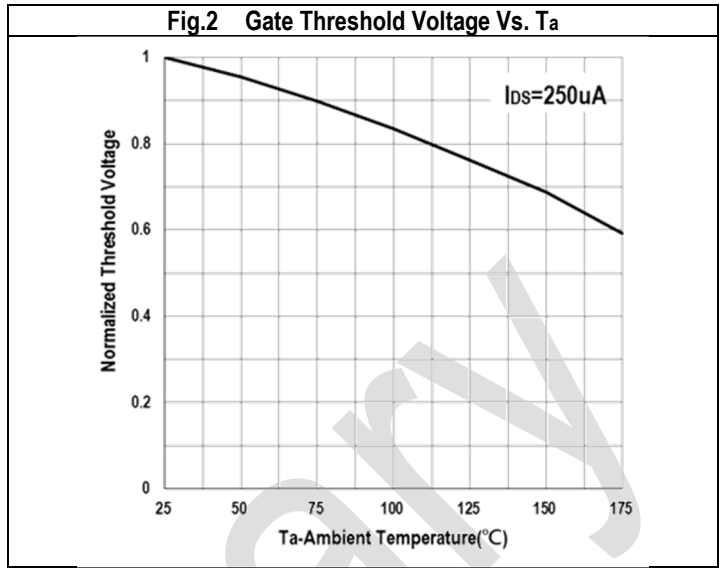
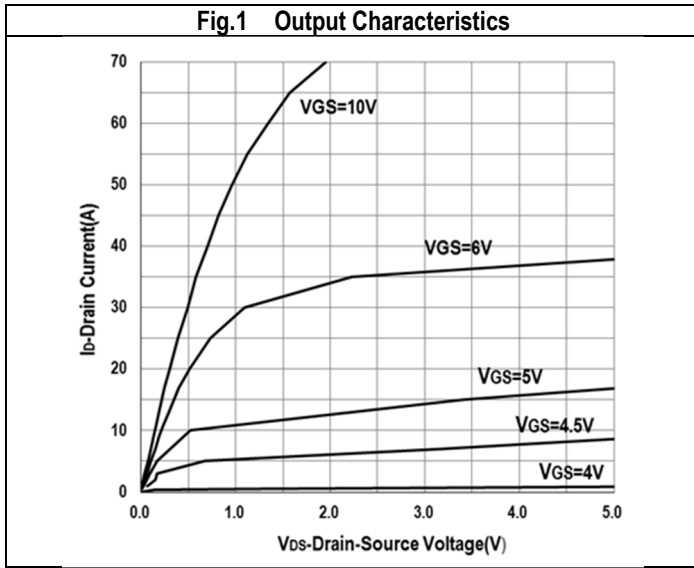
STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =20A	-	16	20	mΩ
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	0.5	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =5V, I _{DS} =20A	-	9	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	760	-	pF
Output Capacitance	C _{oss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	163	-	pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	27	-	pF
Turn-On Delay Time	T _{d(on)}	V _{DS} =50V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	7.9	-	nS
Rise Time	t _r	V _{DS} =50V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	26.3	-	nS
Turn-Off Delay Time	T _{d(off)}	V _{DS} =50V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	11.6	-	nS
Fall Time	t _f	V _{DS} =50V, V _{GS} =10V, I _{DS} =20A, R _{GEN} =3Ω	-	17.8	-	nS

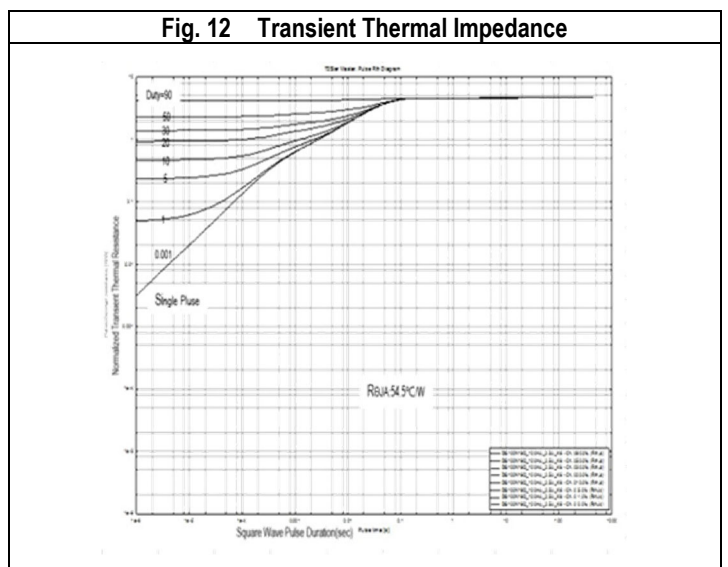
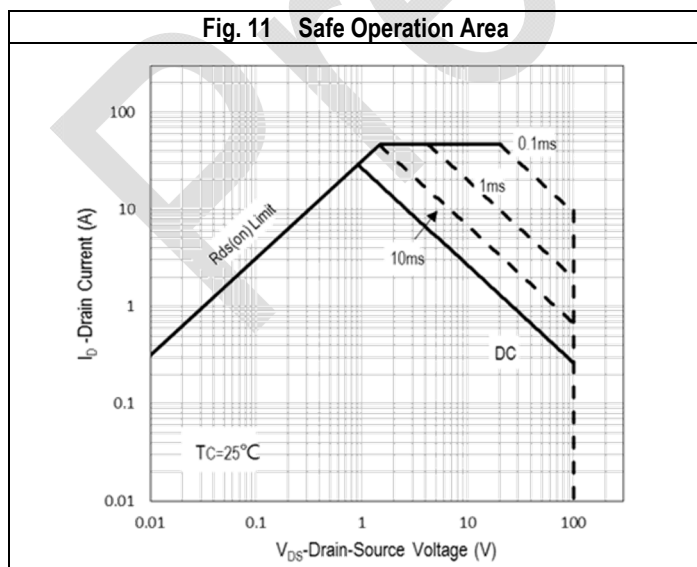
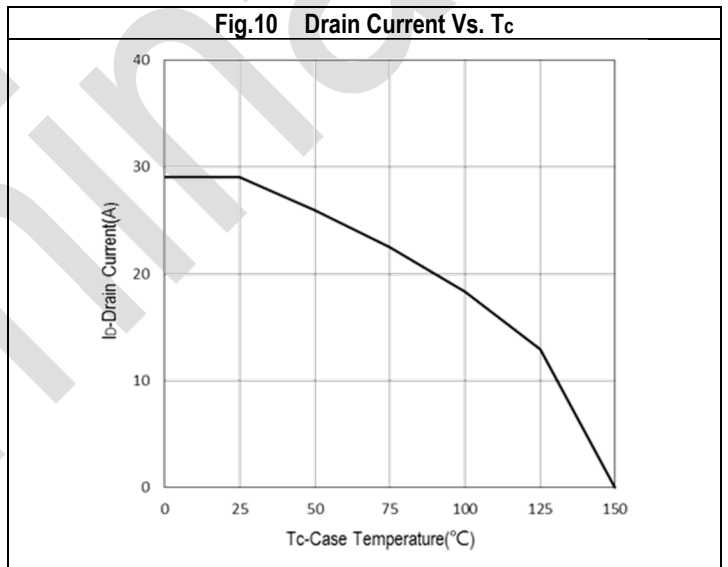
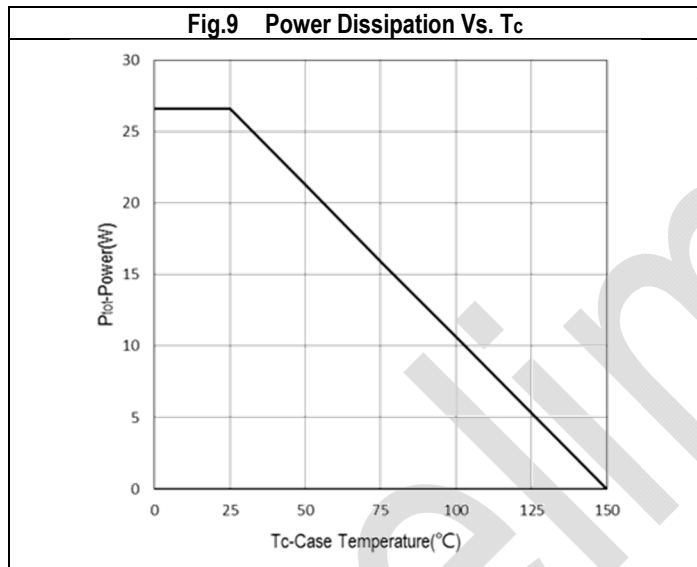
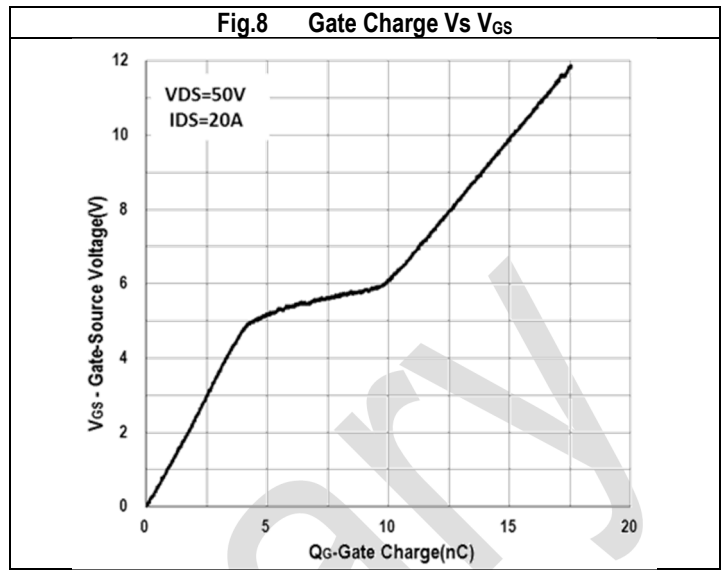
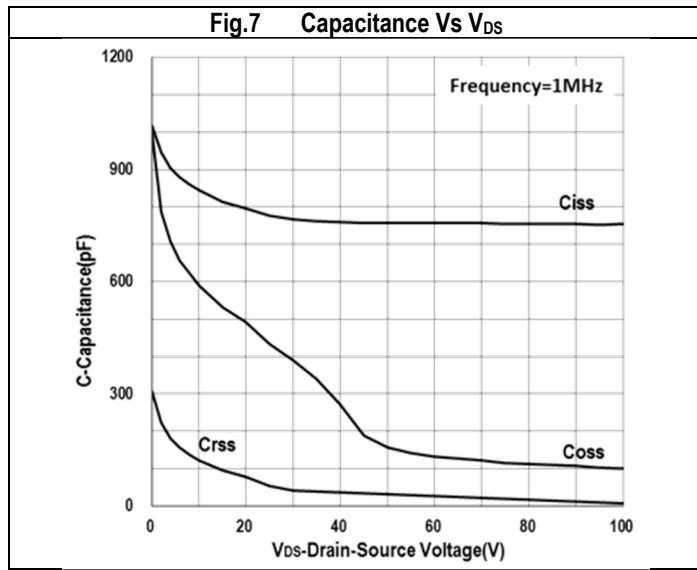
GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate to Source Gate Charge	Q _{gs}	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	4.5	-	nC
Gate charge at threshold	Q _{g(th)}	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	2.6	-	nC
Gate to Drain Charge	Q _{gd}	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	5.6	-	nC
Switching charge	Q _{sw}	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	7.6	-	nC
Gate charge total	Q _g	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	15.6	-	nC
Gate plateau voltage	V _{plateau}	V _{DD} =50V, I _D =20A, V _{GS} =0 to 10V	-	5.6	-	V
Gate charge total, sync. FET (Q _g - Q _{gd})	Q _{g(sync)}		-	9.9	-	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Body Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A	-	0.7	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =60V, I _F =20A, di/dt=100A/μs	-	36.1	-	nS
		V _{DD} =60V, I _F =20A, di/dt=200A/μs	-	31.9	-	nS
Body Diode Reverse Recovery Charge	Q _{rr}	V _{DD} =60V, I _F =20A, di/dt=100A/μs	-	31.2	-	nC
		V _{DD} =60V, I _F =20A, di/dt=200A/μs	-	61.8	-	nC


Typical Operating Characteristics



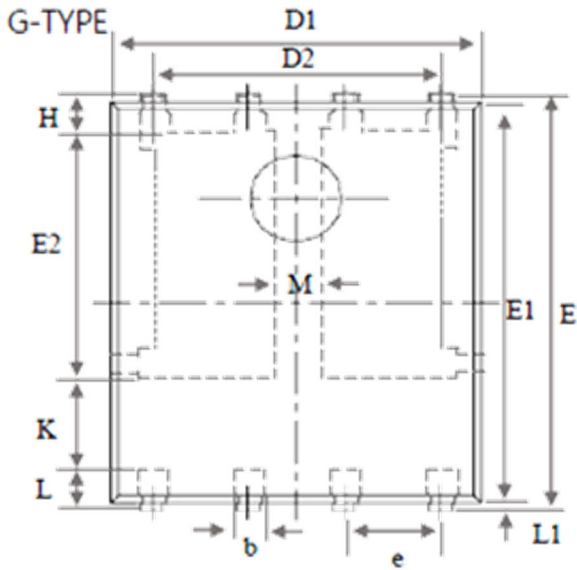
Typical Operating Characteristics (Cont.)



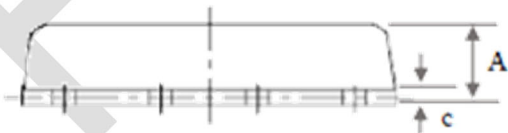
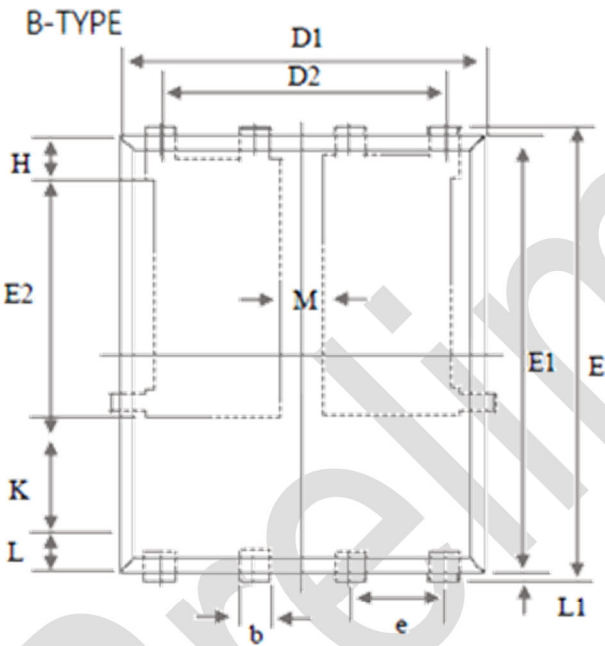
Marking Information

PDFN5x6-8L (QD)	Marking Rule
<p>Laser Marking</p> 	<p><u>Line 1</u> : Device 100N14HQD</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

Package of Dimension



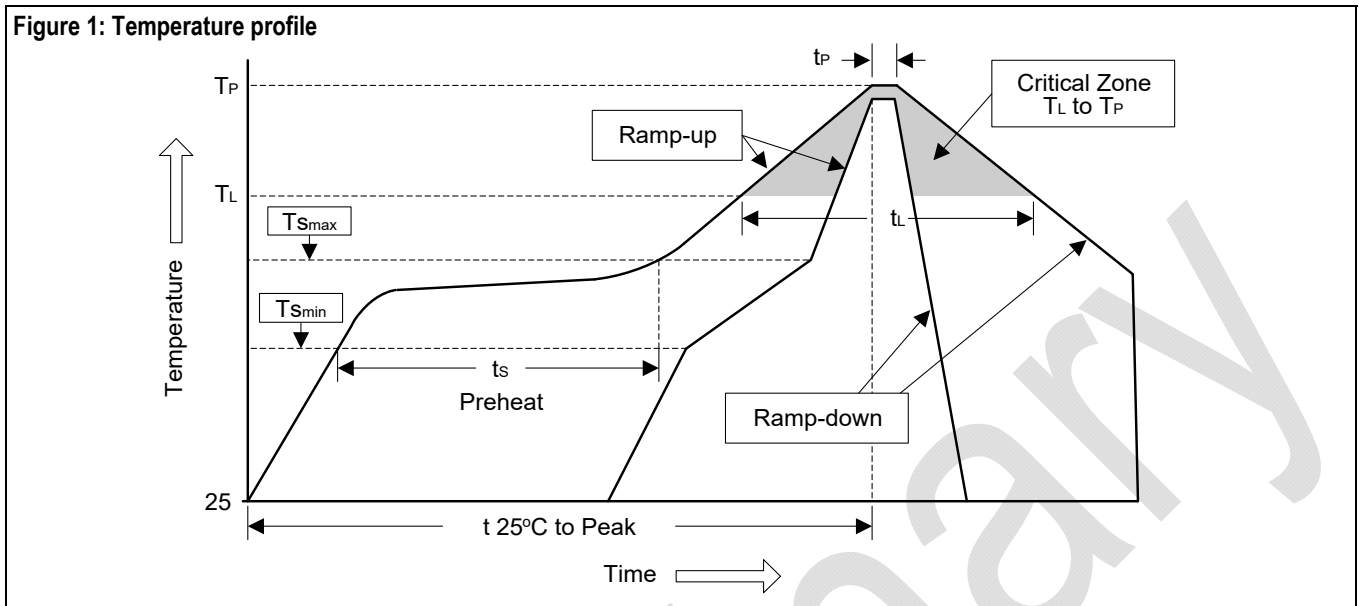
Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
c	0.203 BSC		
D1	4.80	4.90	5.00
D2	3.61	3.96	4.30
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
K	1.10	-	-
L	0.38	0.56	0.74
L1	0.50	0.38	0.25
M	0.50	-	-



1. All dimension are in millimeters.
2. Dimension does not include burrs and mold flash/protrusions.

Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60 to 120 sec	60 to 180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_p)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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